

N-Channel JFET Low-Frequency Low-Noise Amplifier

BSR57

• This device is designed for low–power chopper or switching application sourced from process 51

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C unless otherwise noted)

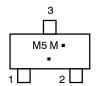
Parameter	Symbol	Value	Unit
Drain-Gate Voltage	V_{DGO}	40	V
Gate-Source Voltage	V_{GSO}	-40	V
Forward Gate Current	I_{GF}	50	mA
Total Power Dissipation Up to T _{amb} = 40°C	P _{tot}	250	mW
Storage Temperature Range	T _{STG}	-55 to +150	°C
Junction Temperature	TJ	150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



- 1. Drain
- Source
 Gate
- SOT-23 CASE 318-08 STYLE 10

MARKING DIAGRAM



M5 = Specific Device Code

M = Date Code ■ Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package Shipping [†]	
BSR57	SOT-23-3/5 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV _{GSS}	Gate-Source Voltage	$V_{DS} = 0 \text{ V}, I_{C} = 1.0 \mu\text{A}$	40	-	-	V
I _{GSS}	Gate Reverse Current	V _{GS} = 20 V, V _{DS} = 0 V	-	-	1.0	nA
I _{DSS}	Zero-Gate Voltage Drain Current	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}$	20	-	100	mA
V _{GS} (off)	Gate-Source Cut-off Voltage	$V_{DS} = 15 \text{ V}, I_D = 0.5 \text{ nA}$	2.0	-	6.0	V
V _{DS} (on)	Drain-Source On Voltage	$V_{GS} = 0 \text{ V}, I_D = 10 \text{ mA}$	-	-	0.5	V
r _{ds} (on)	Drain-Source On Reverse	$V_{GS} = 0 \text{ V}, I_D = 1 \text{ mA}$	-	-	40	Ω
C _{rss}	Reverse Transfer Capacitance	$V_{DS} = 0 \text{ V}, V_{GS} = 10 \text{ V}$	-	-	5.0	pF
t _d	Delay Time	$V_{DD} = 10 \text{ V}, V_{GS}(on) = 0 \text{ V}$	-	-	6.0	ns
t _r	Rise Time	$I_D = 10 \text{ mA}, V_{GS}(\text{off}) = 6.0 \text{ V}$	_	_	4.0	
t _{off}	Turn-off Time		_	-	50	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1

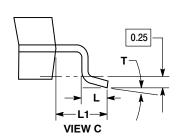


SOT-23 (TO-236) CASE 318-08 **ISSUE AS**

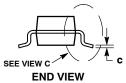
DATE 30 JAN 2018

SCALE 4:1 D - 3X b

TOP VIEW







RECOMMENDED SOLDERING FOOTPRINT



DIMENSIONS: MILLIMETERS

NOTES:

- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
 2. CONTROLLING DIMENSION: MILLIMETERS.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH.
 MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0°		10°	0°		10°

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

= Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot " ■", may or may not be present.

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	ı	
STYLE 9:	STYLE 10:	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN		PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE		2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE		3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE		PIN 1. NO CONNECTION	I PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE		2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE		3. ANODE	3. CATHODE-ANODE	5. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE				

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DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 1	

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